

MOSFETs Silicon N-Channel MOS

# SSM3K59CTB

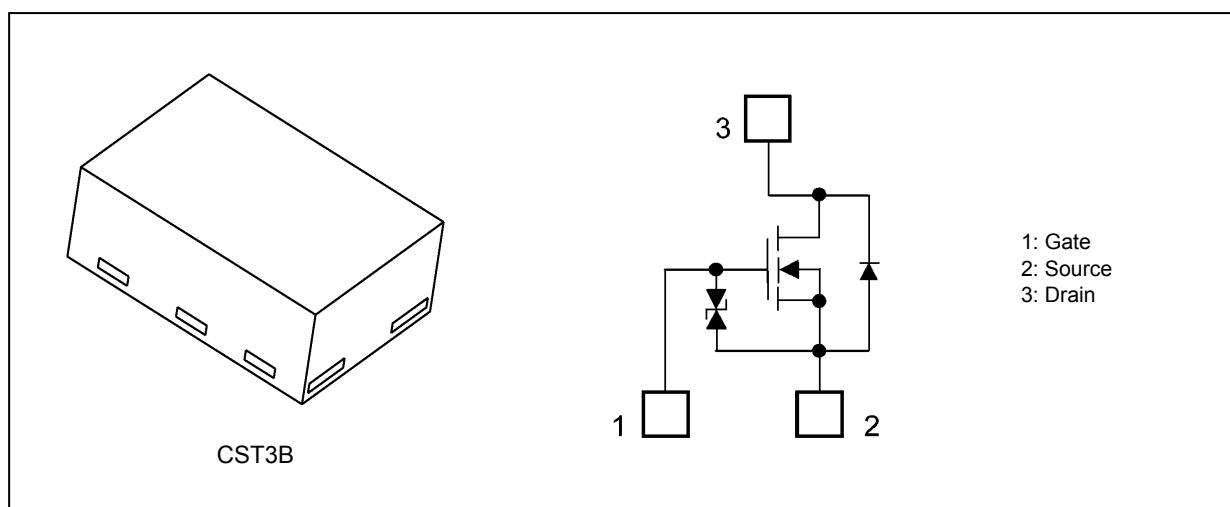
## 1. Applications

- DC-DC Converters

## 2. Features

- 1.8-V gate drive voltage.
- Low drain-source on-resistance
  - $R_{DS(ON)} = 250 \text{ m}\Omega$  (typ.) (@ $V_{GS} = 1.8 \text{ V}$ ,  $I_D = 0.2 \text{ A}$ )
  - $R_{DS(ON)} = 210 \text{ m}\Omega$  (typ.) (@ $V_{GS} = 2.5 \text{ V}$ ,  $I_D = 0.5 \text{ A}$ )
  - $R_{DS(ON)} = 185 \text{ m}\Omega$  (typ.) (@ $V_{GS} = 4.5 \text{ V}$ ,  $I_D = 1.0 \text{ A}$ )
  - $R_{DS(ON)} = 175 \text{ m}\Omega$  (typ.) (@ $V_{GS} = 8.0 \text{ V}$ ,  $I_D = 1.0 \text{ A}$ )

## 3. Packaging and Pin Assignment



## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25 \text{ }^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	40	V
Gate-source voltage	$V_{GSS}$	$\pm 12$	
Drain current (DC)	$I_D$	2.0	A
Drain current (pulsed)	$I_{DP}$	4.0	
Power dissipation	$P_D$	1000	mW
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Ensure that the channel temperature does not exceed 150  $^\circ\text{C}$ .

Note 2: Device mounted on an FR4 board. (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu pad: 645 mm $^2$ )

Start of commercial production  
2015-01

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the drain power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

## 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 10\text{ V}$ , $V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = 40\text{ V}$ , $V_{GS} = 0\text{ V}$	—	—	1	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 1\text{ mA}$ , $V_{GS} = 0\text{ V}$	40	—	—	V
Drain-source breakdown voltage (Note 1)	$V_{(BR)DSX}$	$I_D = 1\text{ mA}$ , $V_{GS} = -12\text{ V}$	25	—	—	V
Gate threshold voltage (Note 2)	$V_{th}$	$V_{DS} = 3\text{ V}$ , $I_D = 1\text{ mA}$	0.5	—	1.2	V
Drain-source on-resistance (Note 3)	$R_{DS(ON)}$	$I_D = 1.0\text{ A}$ , $V_{GS} = 8.0\text{ V}$	—	175	215	$\text{m}\Omega$
		$I_D = 1.0\text{ A}$ , $V_{GS} = 4.5\text{ V}$	—	185	228	
		$I_D = 1.0\text{ A}$ , $V_{GS} = 4.2\text{ V}$	—	186	231	
		$I_D = 1.0\text{ A}$ , $V_{GS} = 3.6\text{ V}$	—	190	238	
		$I_D = 0.5\text{ A}$ , $V_{GS} = 2.5\text{ V}$	—	210	268	
		$I_D = 0.2\text{ A}$ , $V_{GS} = 1.8\text{ V}$	—	250	420	
Forward transfer admittance (Note 3)	$ Y_{fs} $	$V_{DS} = 3\text{ V}$ , $I_D = 200\text{ mA}$	—	2	—	S

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

Take this into consideration when using the device.

Note 3: Pulse measurement.

### 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	—	130	—	$\text{pF}$
Reverse transfer capacitance	$C_{rss}$		—	7.5	—	
Output capacitance	$C_{oss}$		—	26	—	
Switching time (turn-on time)	$t_{on}$	$V_{DD} = 10\text{ V}$ , $I_D = 0.5\text{ A}$ , $V_{GS} = 0$ to $2.5\text{ V}$ , $R_G = 4.7\text{ }\Omega$	—	13	—	$\text{ns}$
Switching time (turn-off time)	$t_{off}$		—	8	—	

### 5.3. Switching Time Test Circuit

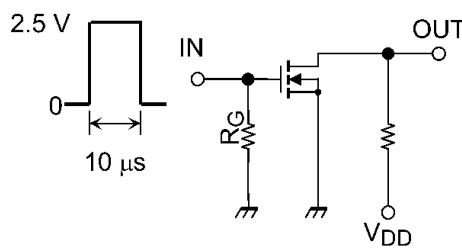


Fig. 5.3.1 Switching Time Test Circuit

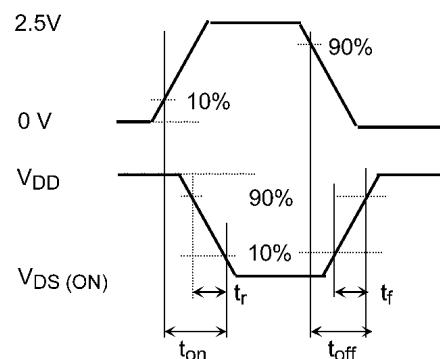


Fig. 5.3.2 Input Waveform/Output Waveform

#### 5.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} = 10\text{ V}$ , $I_D = 1.8\text{ A}$ , $V_{GS} = 4.2\text{ V}$	—	1.1	—	nC
Gate-source charge 1	$Q_{gs1}$		—	0.18	—	
Gate-drain charge	$Q_{gd}$		—	0.5	—	

#### 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Diode forward voltage (Note 1)	$V_{DSF}$	$I_D = -2.0\text{ A}$ , $V_{GS} = 0\text{ V}$	—	-0.85	-1.2	V

Note 1: Pulse measurement.

#### 6. Marking

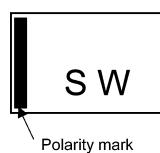


Fig. 6.1 Marking

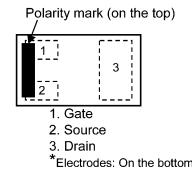
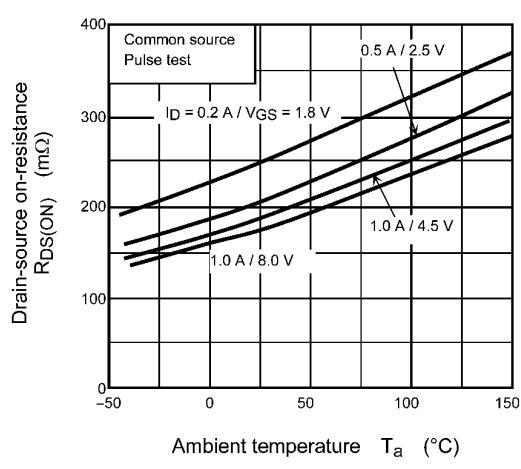
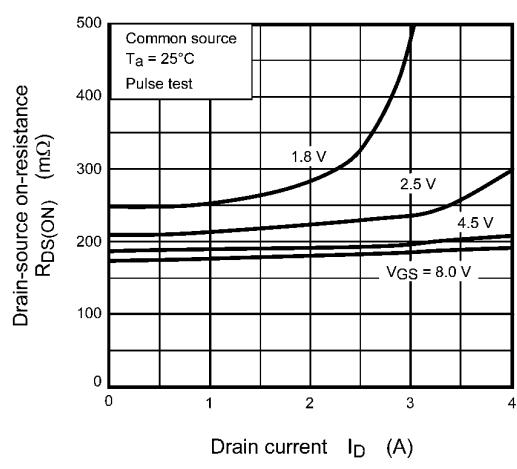
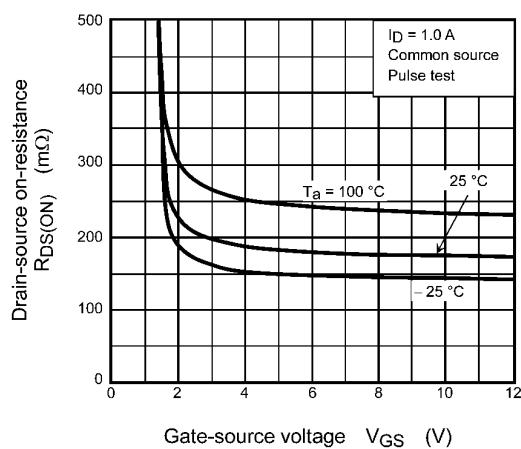
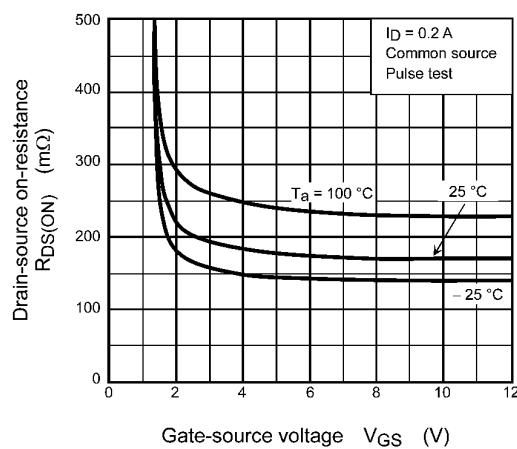
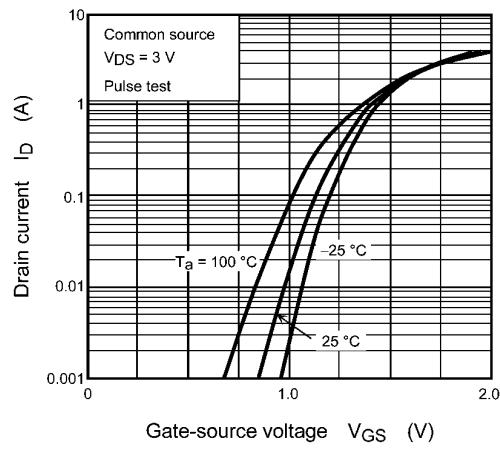
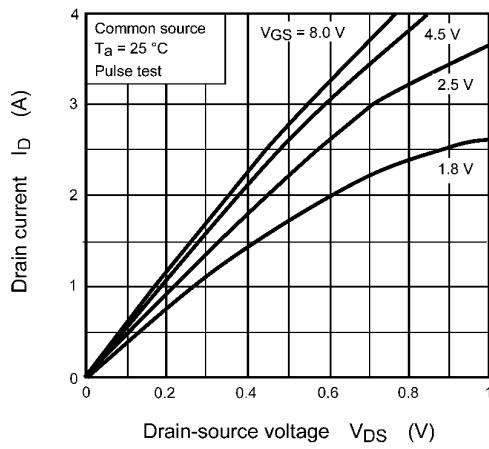


Fig. 6.2 Pin Condition (top view)

## 7. Characteristics Curves (Note)



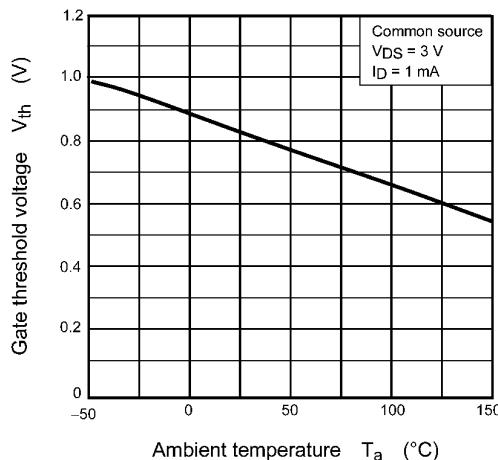
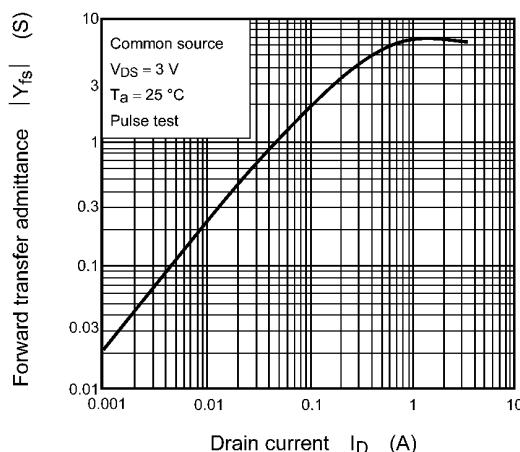
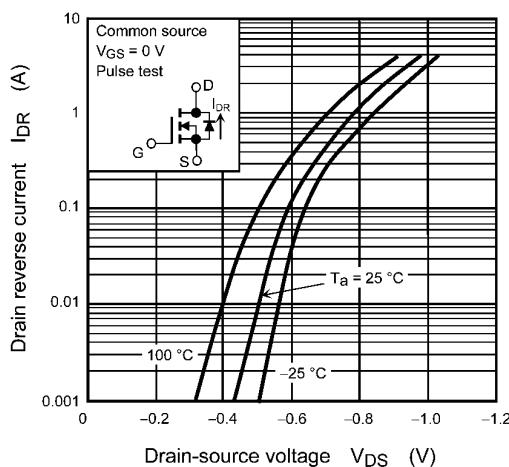
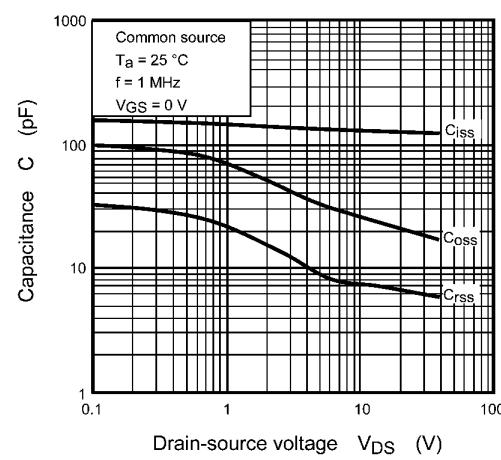
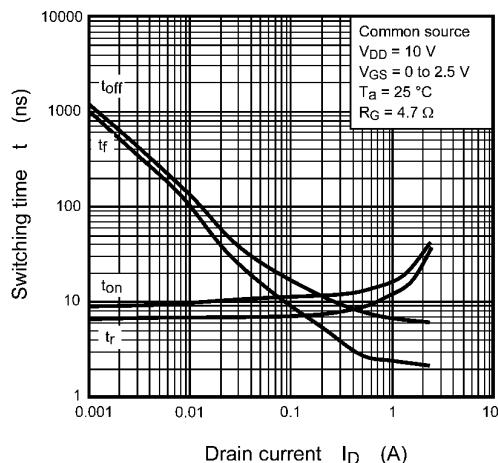
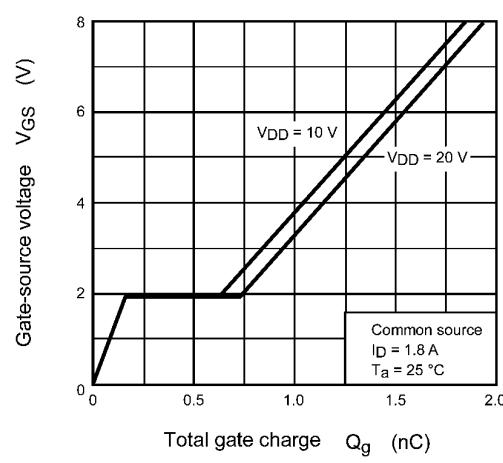
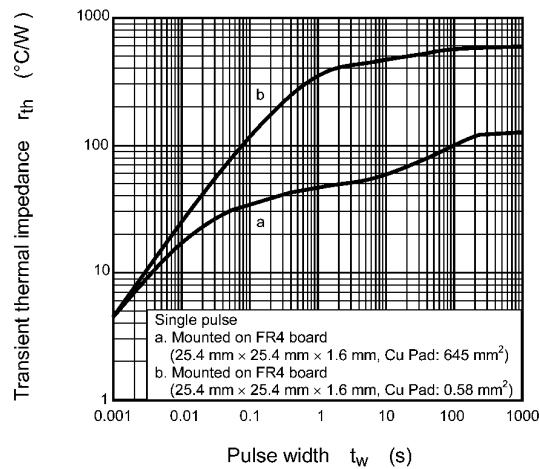
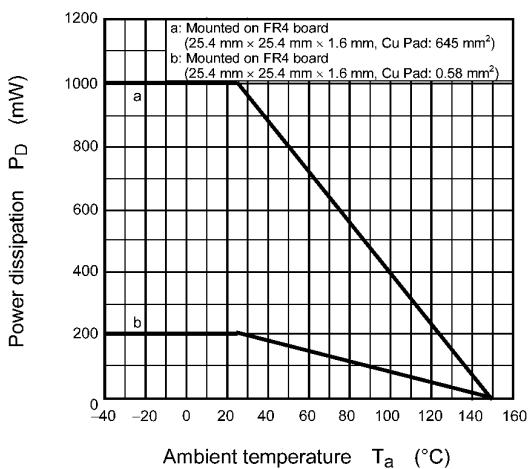
Fig. 7.7  $V_{th}$  -  $T_a$ Fig. 7.8  $|Y_{fs}|$  -  $I_D$ Fig. 7.9  $I_{DR}$  -  $V_{DS}$ Fig. 7.10  $C$  -  $V_{DS}$ Fig. 7.11  $t$  -  $I_D$ 

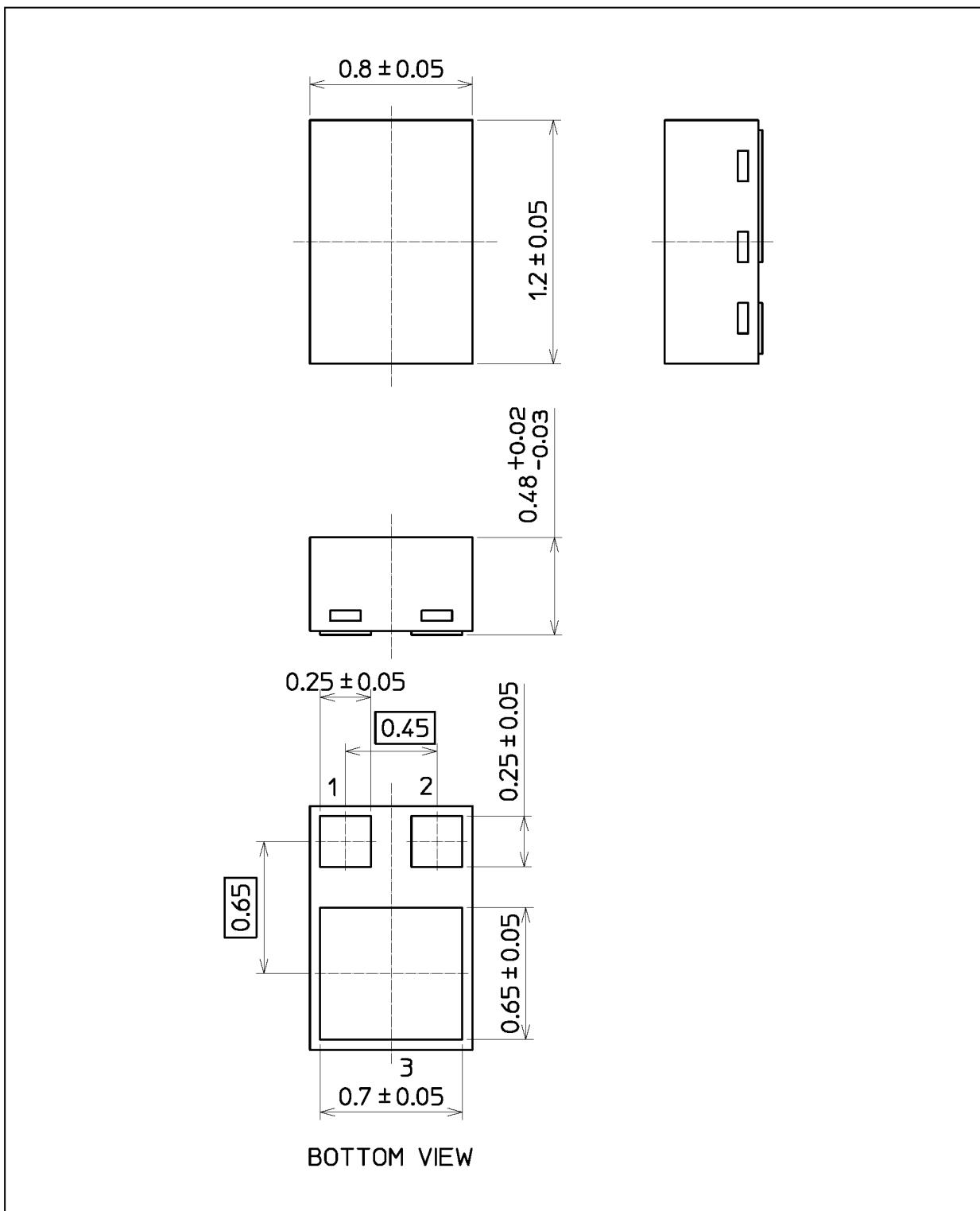
Fig. 7.12 Dynamic Input Characteristics

Fig. 7.13  $r_{th}$  -  $t_w$ Fig. 7.14  $P_D$  -  $T_a$ 

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 0.75 mg (typ.)

Package Name(s)
Nickname: CST3B

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